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# IMPORTANT NOTICE

10 December 2015

## 1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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**Email** - For [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com) use [salesaddresses@ween-semi.com](mailto:salesaddresses@ween-semi.com)

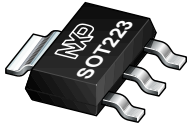
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Thank you for your cooperation and understanding,

WeEn Semiconductors





# EC103D1W

SCR

23 July 2014

Product data sheet

## 1. General description

Planar passivated ultra sensitive gate Silicon Controlled Rectifier in a SOT223 surface mountable plastic package.

## 2. Features and benefits

- Planar passivated for voltage ruggedness and reliability
- Ultra sensitive gate
- Surface mountable package

## 3. Applications

- Electronic ballasts
- Safety shut down and protection circuits
- Sensing circuits
- Smoke detectors
- Switched Mode Power Supplies

## 4. Quick reference data

Table 1. Quick reference data

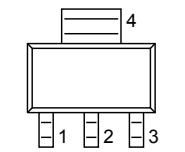

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	400	V
$V_{RRM}$	repetitive peak reverse voltage		-	-	400	V
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	8	A
$T_j$	junction temperature		-	-	125	°C
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{sp} \leq 114\text{ °C}$ ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	0.8	A
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	3	12	$\mu\text{A}$



Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 268\text{ V}$ ; $T_j = 125\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	-	150	-	V/ $\mu$ s

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 <p>SC-73 (SOT223)</p>	
2	A	anode		
3	G	gate		
4	mb	mounting base; connected to anode		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
EC103D1W	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

## 7. Marking

Table 4. Marking codes

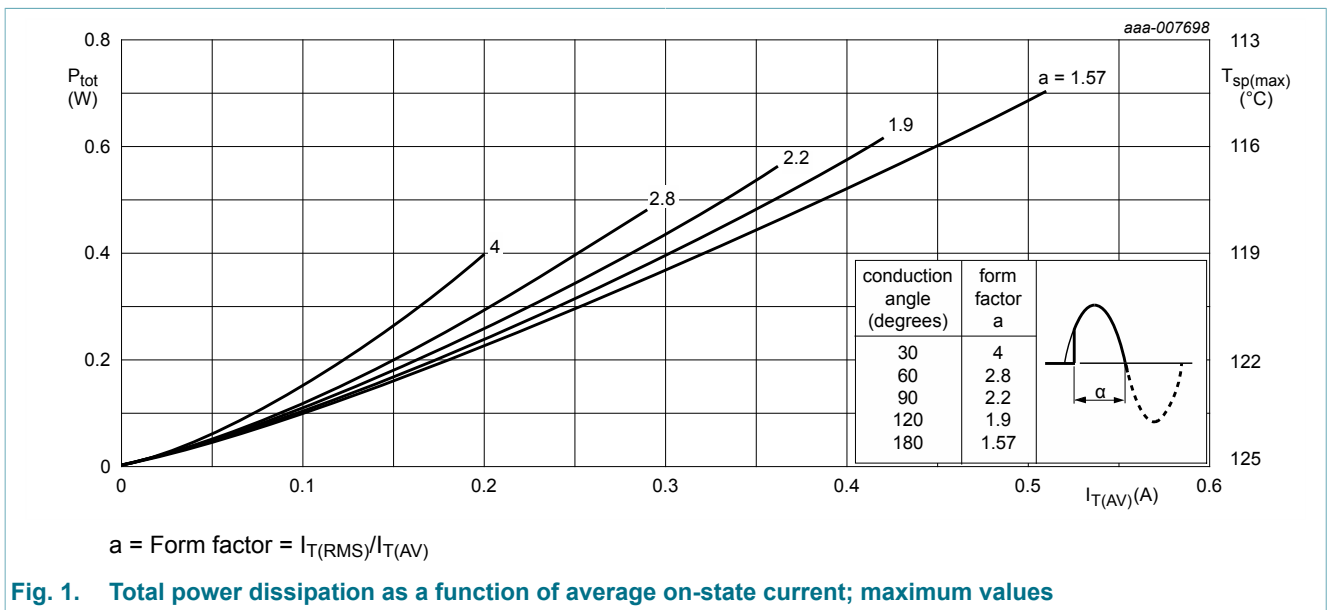
Type number	Marking code
EC103D1W	WYM-103D1W

## 8. Limiting values

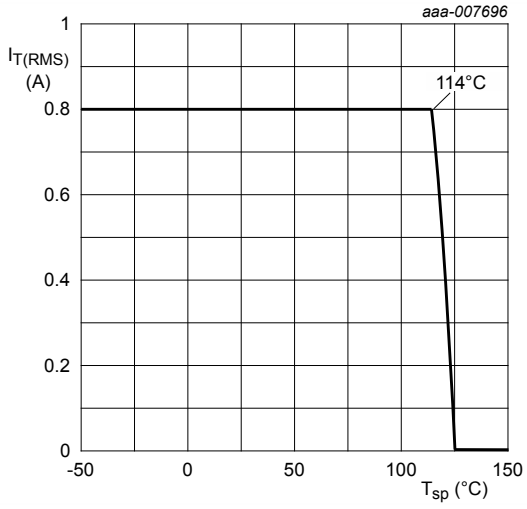
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

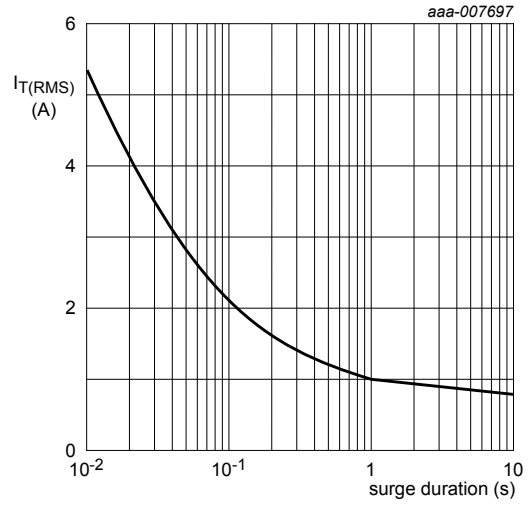
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	400	V
$V_{RRM}$	repetitive peak reverse voltage		-	400	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{sp} \leq 114\text{ °C}$ ; <a href="#">Fig. 1</a>	-	0.5	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{sp} \leq 114\text{ °C}$ ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	0.8	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	8	A
		half sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 8.3\text{ ms}$	-	9	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse	-	0.32	A <sup>2</sup> s
$di_T/dt$	rate of rise of on-state current	$I_T = 2\text{ A}$ ; $I_G = 0.01\text{ A}$ ; $di_G/dt = 0.1\text{ A}/\mu\text{s}$	-	50	A/ $\mu\text{s}$
$I_{GM}$	peak gate current		-	1	A
$V_{RGM}$	peak reverse gate voltage		-	5	V
$P_{GM}$	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
$T_{stg}$	storage temperature		-40	150	°C
$T_j$	junction temperature		-	125	°C



**Fig. 1. Total power dissipation as a function of average on-state current; maximum values**

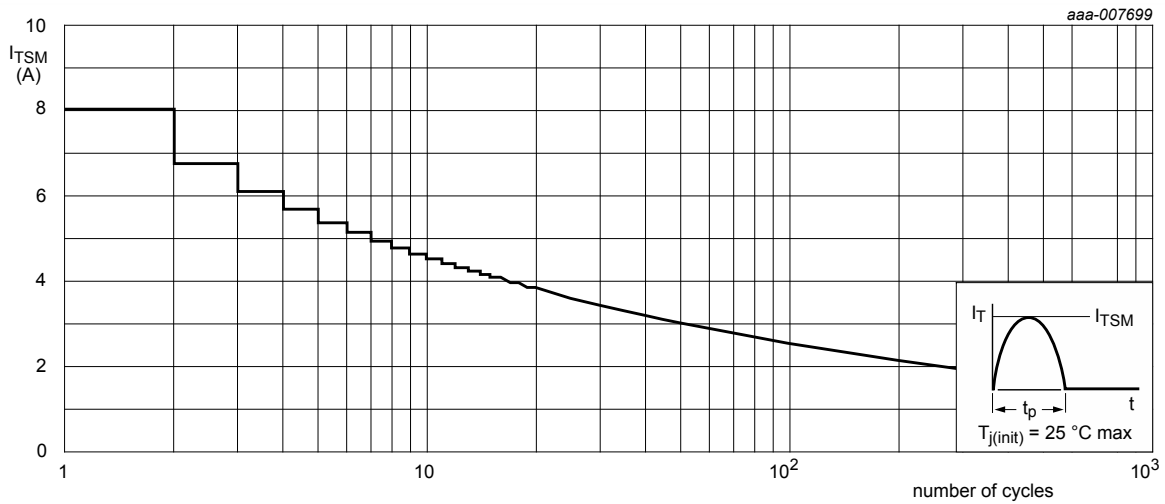


**Fig. 2. RMS on-state current as a function of solder point temperature; maximum values**



$f = 50 \text{ Hz}; T_{sp} = 114 \text{ °C}$

**Fig. 3. RMS on-state current as a function of surge duration; maximum values**



$f = 50 \text{ Hz}$

**Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values**

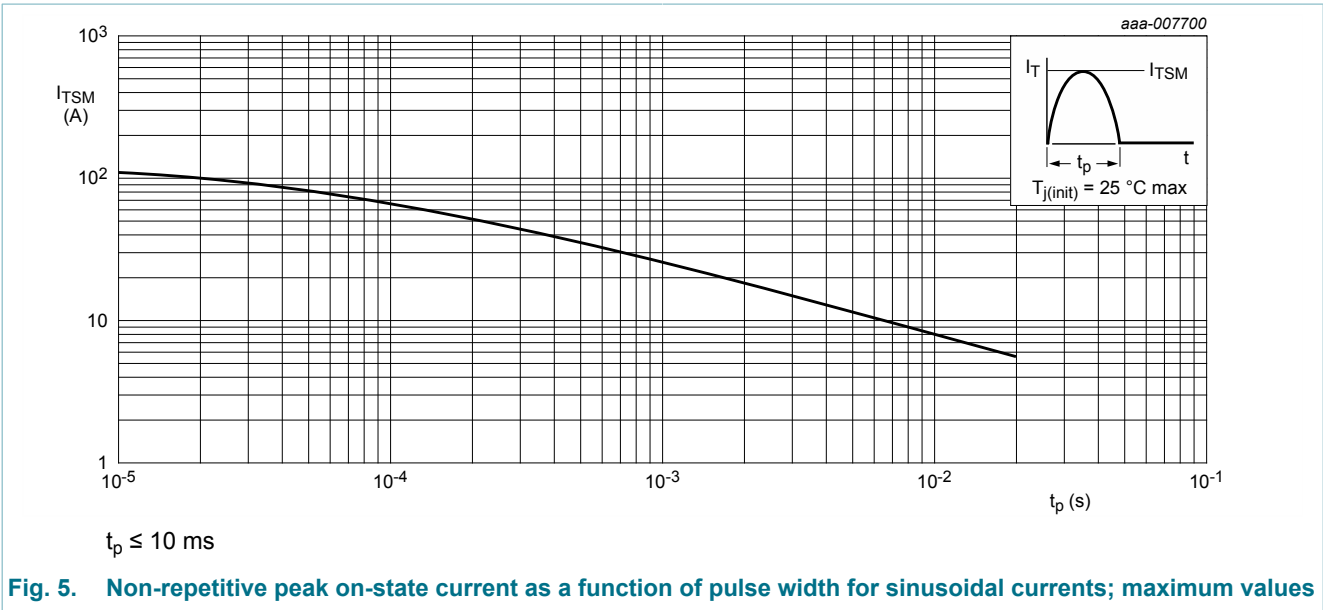


Fig. 5. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	<a href="#">Fig. 6</a>	-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	printed circuit board mounted; minimum pad area; in free air; <a href="#">Fig. 7</a>	-	70	-	K/W
		printed circuit board mounted; minimum footprint; in free air; <a href="#">Fig. 8</a>	-	156	-	K/W

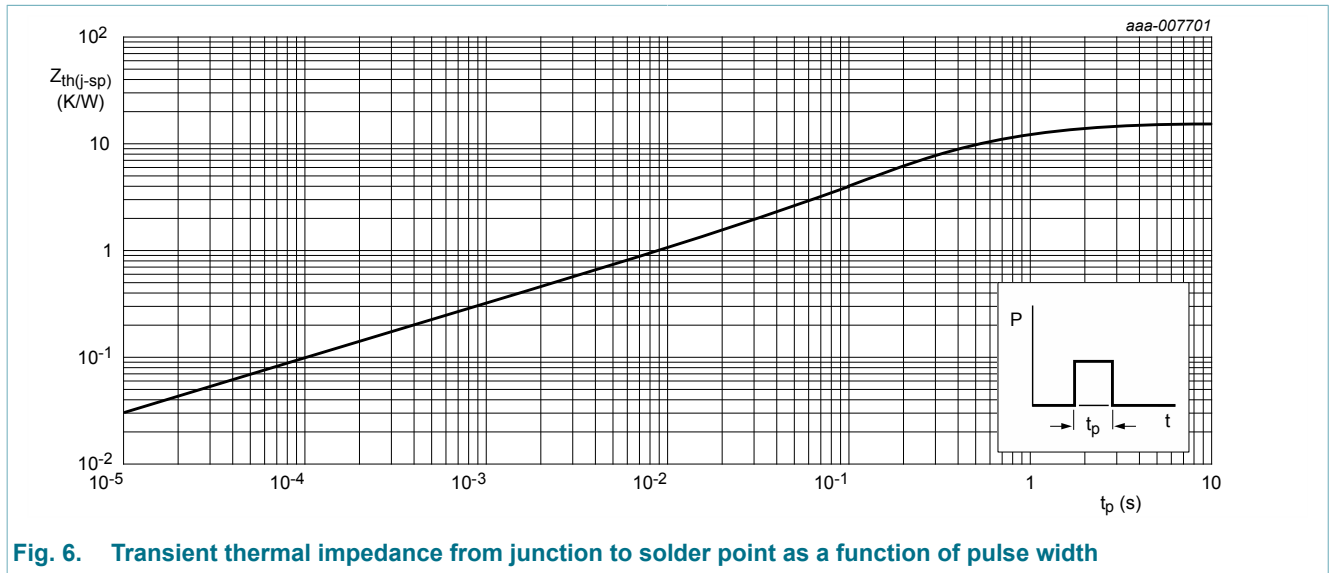
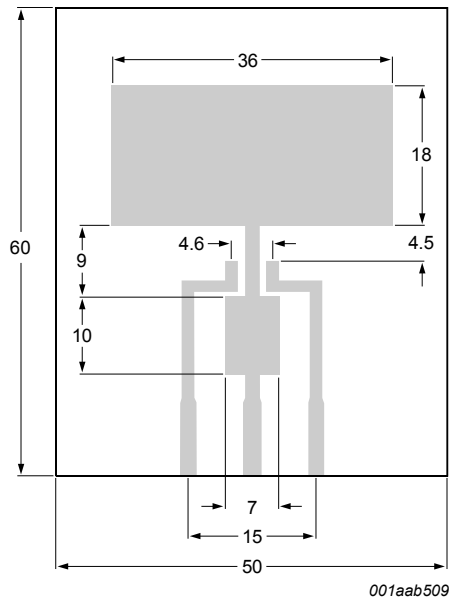


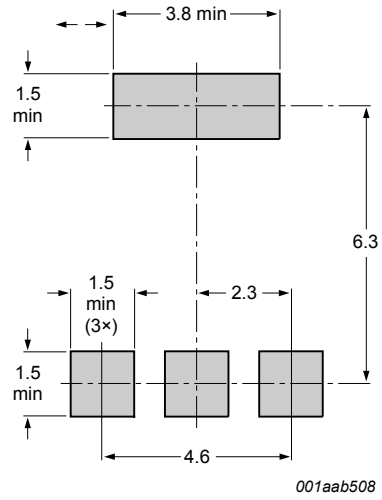
Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width





All dimensions are in mm  
 Printed circuit board:  
 FR4 epoxy glass (1.6 mm thick), copper laminate  
 (35 µm thick)

**Fig. 7. Printed circuit board pad area: SOT223**



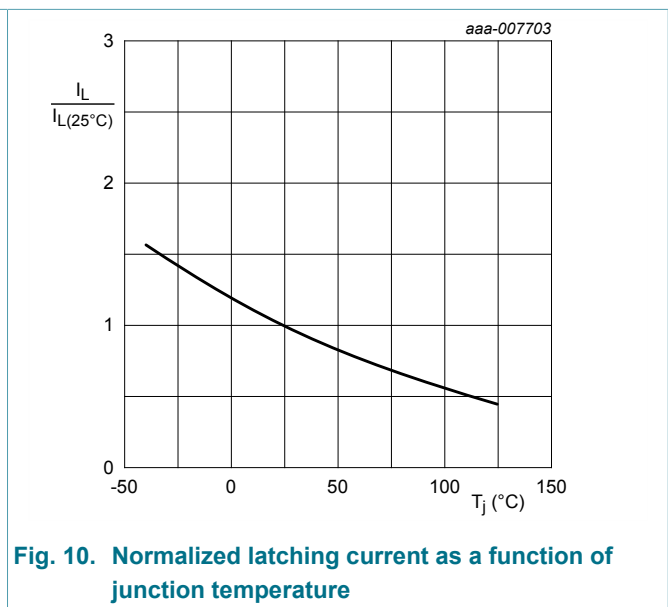
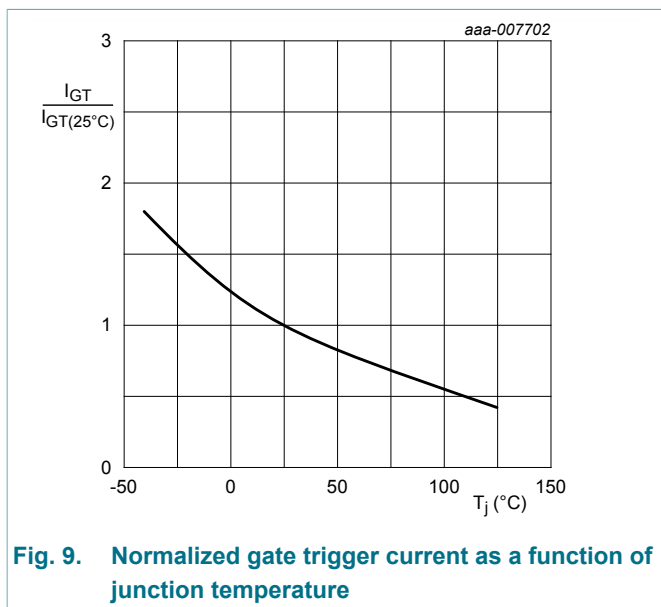
All dimensions are in mm

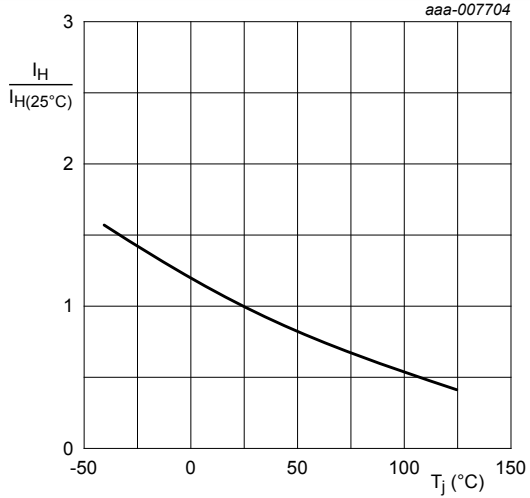
**Fig. 8. Minimum footprint SOT223**

## 10. Characteristics

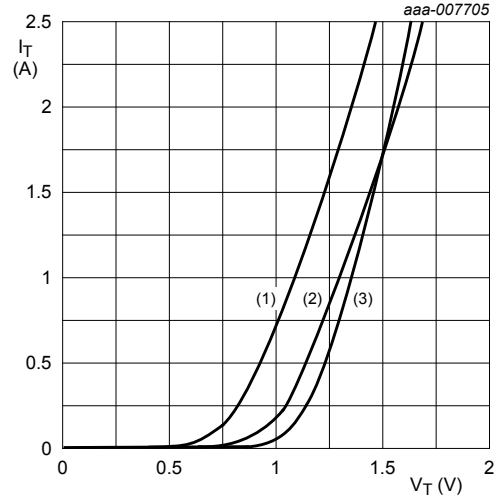
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>	-	3	12	$\mu\text{A}$
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>	-	2	6	$\text{mA}$
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>	-	2	5	$\text{mA}$
$V_T$	on-state voltage	$I_T = 1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>	-	1.2	1.35	$\text{V}$
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 13</a>	-	0.5	0.8	$\text{V}$
		$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; <a href="#">Fig. 13</a>	0.2	0.3	-	$\text{V}$
$I_D$	off-state current	$V_D = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$	-	0.05	0.1	$\text{mA}$
$I_R$	reverse current	$V_R = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$	-	0.05	0.1	$\text{mA}$
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 268\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	-	150	-	$\text{V}/\mu\text{s}$





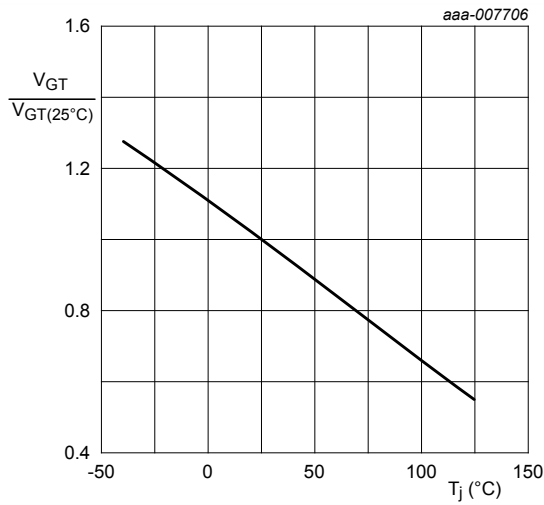
**Fig. 11. Normalized holding current as a function of junction temperature**



$V_o = 0.987 \text{ V}$ ;  $R_s = 0.3125 \ \Omega$

- (1)  $T_j = 125 \text{ }^\circ\text{C}$ ; typical values
- (2)  $T_j = 125 \text{ }^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25 \text{ }^\circ\text{C}$ ; maximum values

**Fig. 12. On-state current as a function of on-state voltage**



**Fig. 13. Normalized gate trigger voltage as a function of junction temperature**

### 11. Package outline

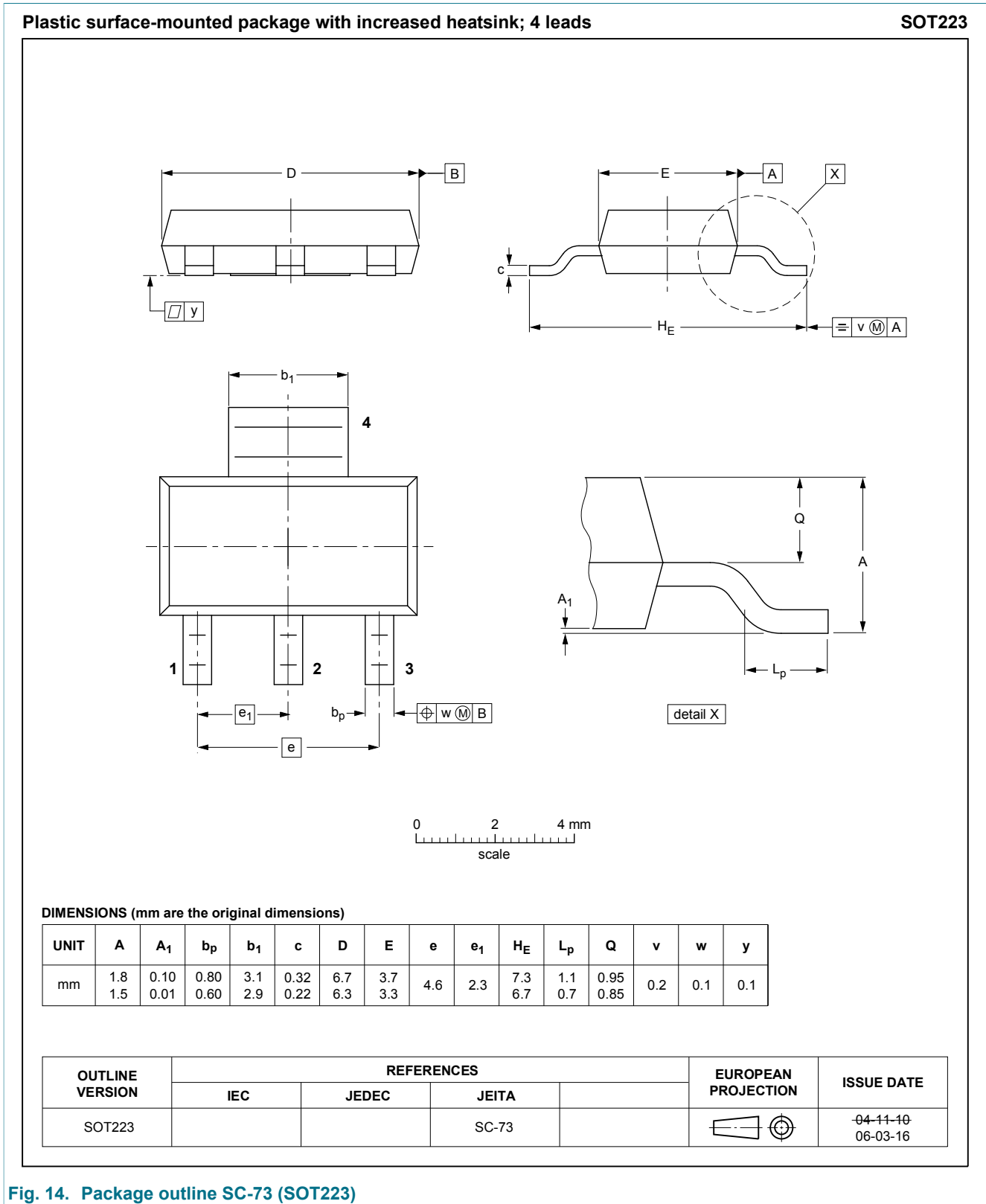


Fig. 14. Package outline SC-73 (SOT223)

## 12. Legal information

### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 23 July 2014